L Number	Hits	Search Text	DB	Time stamp
-	847	((257/204) or (257/206)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:12
-	20	(((257/204) or (257/206)).CCLS.) and (silicon near germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:17
-	16007	CMOS and PMOS and NMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:17
-	2	(CMOS and PMOS and NMOS) and (elevat$3 or rais43) near (source or drain) and (stress with channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:18
-	134	(CMOS and PMOS and NMOS) and (stress with channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 12:10
-	1588	CMOS and NFET and PFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 15:30
-	32	(CMOS and NFET and PFET) and (stress with channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 15:35
-	137	toledo.xa.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 15:42
-	296	(elevated near (source or drain)) and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 15:42
-	112	((elevated near (source or drain)) and CMOS) and (SiGe or (silicon near germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:02
-	38	(((elevated near (source or drain)) and CMOS) and (SiGe or (silicon near germanium))) and (PMOS or PFET) and (NMOS or NFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:02
-	6	(("5510630") or ("5641695") or ("6271066")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:18

| - | 184 | PFET and NFET and (silicon near germanium or SiGe) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/11/04 16:19 |